

Silicon PNP Power Transistors

2SB554

DESCRIPTION

- With TO-3 package
- Complement to type 2SD424
- High power dissipation

APPLICATIONS

- For use in power amplifier applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

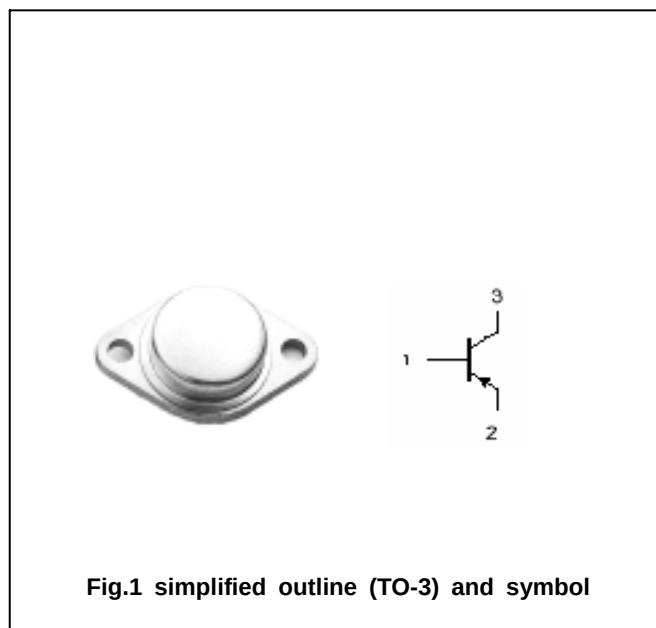


Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings($T_a=^{\circ}\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-180	V
V_{CEO}	Collector-emitter voltage	Open base	-180	V
V_{EBO}	Emitter-base voltage	Open collector	-5	V
I_C	Collector current		-15	A
I_B	Base current		-4	A
P_C	Collector power dissipation	$T_C=25^{\circ}\text{C}$	150	W
T_j	Junction temperature		150	$^{\circ}\text{C}$
T_{stg}	Storage temperature		-55~200	$^{\circ}\text{C}$

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CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=-25mA$; $I_B=0$	-180			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=-10A$; $I_B=-1A$			-3.0	V
V_{BE}	Base-emitter on voltage	$I_C=-2A$; $V_{CE}=-5V$			-1.5	V
I_{CBO}	Collector cut-off current	$V_{CB}=-90V$; $I_E=0$			-0.1	mA
I_{EBO}	Emitter cut-off current	$V_{EB}=-5V$; $I_C=0$			-0.1	mA
h_{FE}	DC current gain	$I_C=-2A$; $V_{CE}=-5V$	40		140	
C_{OB}	Output capacitance	$I_E=0$; $V_{CB}=-10V$; $f=1.0MHz$		450		pF
f_T	Transition frequency	$I_C=-2A$; $V_{CE}=-5V$		6		MHz

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PACKAGE OUTLINE

